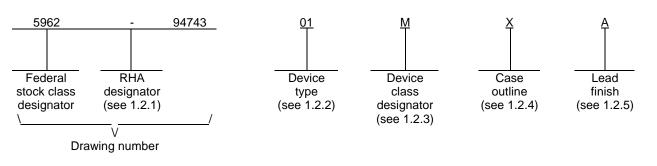
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LTR		DESCRIPTION					DATE (YR-M			R-MO-E	-MO-DA) APPROVED									
A	Drav	Drawing updated to reflect current requirementsrrp						04-06-15		R. MONNIN										
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SHEET REV SHEET				SHE	/ EET PAREE RICK OF		1	A 2	A 3	A 4	5	6	7	8	9	10	11	12	13	
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A	NDA	CUIT		SHE PRE R	EET PARED	FICER	1				5	6 EFEN	7 SE SI	8 JPPL BUS,	9 Y CE	10 NTER	11 218-39	12 .UMB	13	
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRC DRA THIS DRAWII FOR U	NDAI OCIR(AWIN	CUIT IG AVAILA ALL	BLE	SHE PRE R CHE	EET PAREE NCK OF	FICER BY H PITH D BY	1 R HADIA			4 MIC AN	5 DI ROC	6 EFEN CC CIRCI	7 SE SI DLUM http JIT, L DIGI	8 JPPL BUS, o://ww LINE/	9 OHIC w.ds	10 NTER D 432 cc.dla 6-BIT	11 218-39 a.mil	12 -UMB 990) KSF WITH	13 US PS,	N
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1. SCOPE

1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 <u>PIN</u>. The PIN is as shown in the following example:



1.2.1 <u>RHA designator</u>. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function		
01	AD676	16 Bit, analog to digital converter with parallel interface		

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation					
Μ	Vendor self-certification to the requirements for MIL-STD-883 compliant, non- JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A					
Q or V	Certification and qualification to MIL-PRF-38535					
1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:						

Outline letter	utline letter Descriptive designator		Package style
Х	GDIP1-T28 or CDIP2-T28	28	Dual-in-line

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

STANDARD MICROCIRCUIT DRAWING	Α		5962-94743
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		A	2

1.3 Absolute maximum ratings. 1/

V_{CC} to V_{EE}	-0.3 V to +26.4 V
V _{DD} to DGND	-0.3 V to +7 V
V _{CC} to AGND	-0.3 V to +18 V
V _{EE} to AGND	-18 V to +0.3 V
AGND to DGND	±0.3 V
Digital inputs (CAL, SAMPLE, CLK,) to DGND	0 V to +5.5 V
Analog inputs (V_{IN}, V_{REF}, AGND SENSE) to AGND	(V_{CC} + 0.3 V) to (V_{EE} - 0.3 V)
Power dissipation (P _D):	
10 V	630 mW
5 V	480 mW
Storage temperature range	-65°C to +150°C
Lead temperature (soldering, 10 seconds)	+300°C
Thermal resistance, junction-to-case (θ_{JC})	See MIL-STD-1835
Thermal resistance, junction-to-ambient (θ_{JA})	60°C/W

1.4 <u>Recommended operating conditions</u>. <u>2/</u>

Positive analog supply voltage (V _{CC})	11.4 V to 12.6 V
Negative analog supply voltage (V _{EE})	-11.4 V to -12.6 V
Digital supply voltage (V _{DD})	4.5 V to 5.5 V
Analog reference voltage (V _{REF})	5 V to 10 V
Analog input voltage range (V _{IN})	-V_{REF} to V_{REF}
Analog ground sense voltage	-0.1 V to 0.1 V
Ambient operating temperature range (T _A)	-55°C to +125°C

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings. MIL-HDBK-780 - Standard Microcircuit Drawings.

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

2/ AGND and DGND tied at ADC.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-94743
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		A	3

(Copies of these documents are available online at <u>http://assist.daps.dla.mil/quicksearch/</u> or <u>www.dodssp.daps.mil</u> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein.

3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.

3.2.3 <u>Block diagram</u>. The block diagram shall be as specified on figure 2.

3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 <u>Notification of change for device class M</u>. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.

3.9 <u>Verification and review for device class M</u>. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 93 (see MIL-PRF-38535, appendix A).

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-94743
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		A	4

Test	Symbol	$\begin{array}{l} Conditions \ \underline{1}/\\ -55^{\circ}C \leq T_{A} \leq +125^{\circ}C\\ \text{unless otherwise specified} \end{array}$	Group A subgroups	Device type	Lim	iits <u>2</u> /	Unit
					Min	Max	
Logic input high voltage	VIH		1,2,3	01	2.0		V
Logic input low voltage	VIL		1,2,3	01		0.8	V
Logic input current	I _{LIN}	$V_{IH} = 5 V, V_{IL} = 0 V$	1,2,3	01	-10	+10	μA
Logic output high voltage	V _{OH}	I _{OH} = 0.5 mA	1,2,3	01	2.4		V
Logic output low voltage	V _{OL}	I _{OL} = 1.6 mA	1,2,3	01		0.4	V
Power supply current	I _{CC}	V _{REF} = 10 V,	1,2,3	01		24	mA
	I _{EE}	device converting			-24		
	I _{DD}					5	
	I _{CC}	V _{REF} = 5 V,				18	
	I _{EE}	device converting			-18		
	I _{DD}					5	
Voltage reference input	V _{REF}		1,2,3	01	5	10	V
Power dissipation	PD	10 V	1,2,3	01		630	mW
		5 V				480	
Integral nonlinearity	INL	All codes	4	01	-1.5	+1.5	LSB
			5,6		-2	+2	
Differential nonlinearity	DNL	All codes <u>3</u> /	4,5,6	01	16		Bits
Bipolar zero error	B _{PZE}	Code = 32767.5	4	01	-4	+4	LSB
			5,6		-6	+6	
Negative full-scale error	A _N	Code = 0.5	4	01	-4	+4	LSB
			5,6		-6	+6	
Positive full-scale error	A _P	Code = 65535.5	4	01	-4	+4	LSB
			5,6		-6	+6	
Signal to noise distortion	S/(N+D)	f _{IN} = 1 kHz <u>4</u> /	4,5,6	01	89		dB
Total harmonic distortion	THD	f _{IN} = 1 kHz <u>4</u> /	4,5,6	01		-92	dB
Conversion time	t _C	See figure 3	9,11	01	10		μs
			10		13.3		
Clock period	t _{CLK}	See figure 3	9,11	01	480		ns
			10		670		
Calibration time	t _{CA}	See figure 3	9,10,11	01		85,530	t _{CLK}
Sampling time	t _S	See figure 3	9,10,11	01	2		μs
(included in t _c)							ļ
CAL to BUSY delay	t _{CALB}	See figure 3	9,10,11	01		150	ns
BUSY to SAMPLE delay	t _{BS}	See figure 3	9,10,11	01	2		μs
SAMPLE to BUSY	t _{SB}	See figure 3	9,10,11	01		100	ns
Clock high	t _{CH}	See figure 3	9,10,11	01	50		ns
Clock low	t _{CL}	See figure 3	9,10,11	01	50		ns
SAMPLE low to first clock	t _{SC}	See figure 3	9,10,11	01	50		ns

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-94743
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		A	5

TABLE I. <u>Electrical performance characteristics</u> – Continued.	TABLE I.	Electrical	performance	characteristics	- Continued.
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Test	Symbol	$\begin{array}{l} Conditions \ \underline{1}/\\ -55^\circ C \leq T_A \leq +125^\circ C\\ unless \ otherwise \ specified \end{array}$	Group A subgroups	Device type	Lim	its <u>2</u> /	Unit
					Min	Max	
SAMPLE low	t _{SL}	See figure 3.	9,10,11	01	100		ns
CAL high	t _{CALH}	See figure 3.	9,10,11	01	50		ns
Output delay	top	See figure 3.	9,10,11	01		200	ns
Status delay	t _{SD}	See figure 3.	9	01	50		ns
			10,11		40		

<u>1</u>/ Unless otherwise specified, V_{CC} = +12 V, V_{EE} = -12 V, V_{DD} = +5 V, V_{REF} = 10 V, V_{IH} = 2.0 V, and V_{IL} = 0.8 V.

- 2/ The algebraic convention, whereby the most negative value is a minimum and the most positive is a maximum, is used in this table. Negative current shall be defined as conventional current flow out of a device terminal.
- 3/ Minimum resolution for which "No missing codes" is guaranteed.
- <u>4</u>/ V_{IN} = 0.05 dB, f_{IN} = 1 kHz, all measurements referred to a 0 dB (20 V_{P-P}) input signal. The full Nyquist bandwidth is used for all values.

4. VERIFICATION

4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

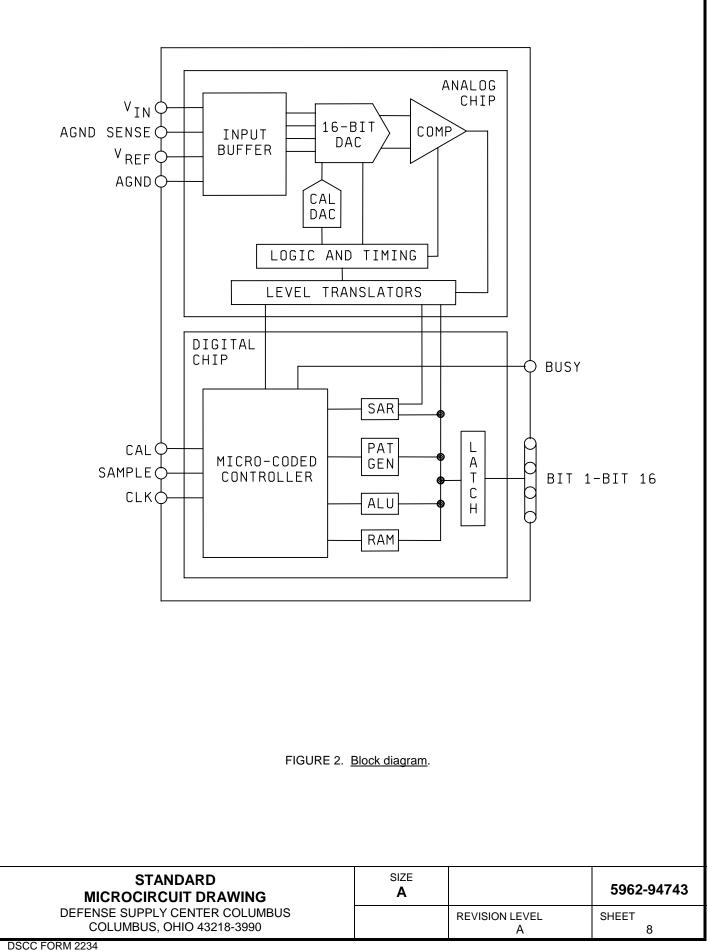
- 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition B. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.

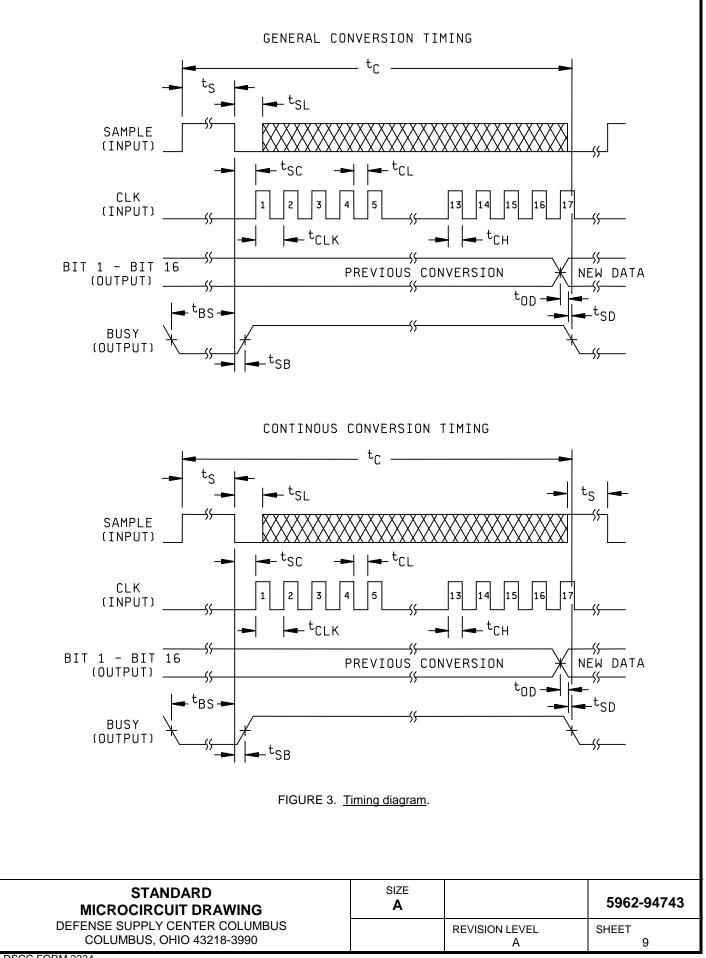
STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-94743
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		A	6

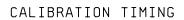
01		
Х		
Terminal symbol		
BIT 11		
BIT 12		
BIT 13		
BIT 14		
BIT 15		
BIT 16 (LSB)		
BUSY		
CAL		
SAMPLE		
CLOCK (CLK)		
DGND		
V _{CC}		
AGND		
AGND SENSE		
V _{IN}		
V _{REF}		
V _{EE}		
V _{DD}		
BIT 1 (MSB)		
BIT 2		
BIT 3		
BIT 4		
BIT 5		
BIT 6		
BIT 7		
BIT 8		
BIT 9		
BIT 10		

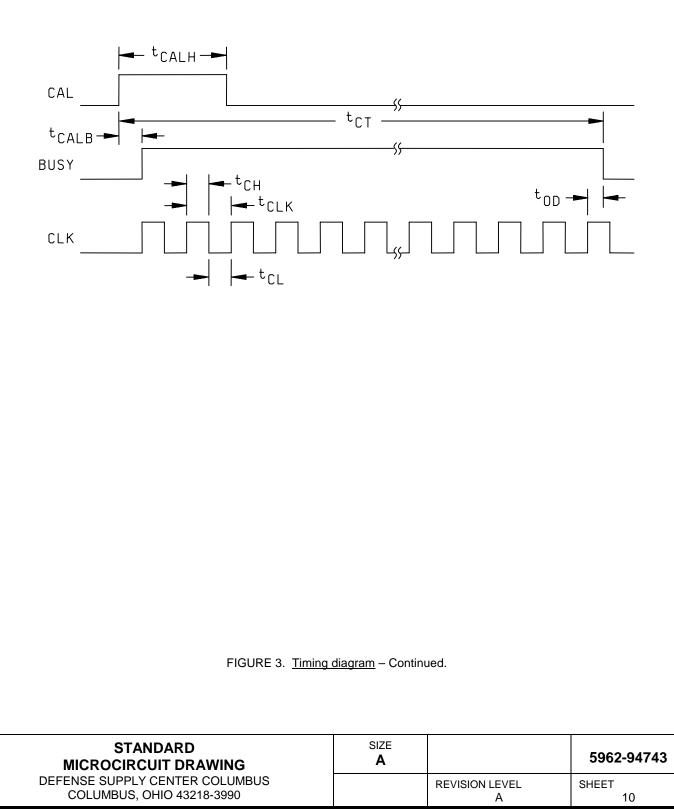
FIGURE 1. Terminal connections.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-94743
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		A	7









- 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. Subgroups 7 and 8 in table I, method 5005 of MIL-STD-883 shall be omitted.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

- a. Test condition B. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
- b. $T_A = +125^{\circ}C$, minimum.
- c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-94743
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		A	11

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device	Device	Device
	class M	class Q	class V
Interim electrical	1	1	1
parameters (see 4.2)			
Final electrical	1,2,3,4,5,6, <u>1</u> /	1,2,3,4,5, <u>1</u> /	1,2,3,4,5, <u>1</u> /
parameters (see 4.2)	9,10,11	6,9,10,11	6,9,10,11
Group A test	1,2,3,4,5,6,	1,2,3,4,5,	1,2,3,4,5,
requirements (see 4.4)	9,10,11	6,9,10,11	6,9,10,11
Group C end-point electrical	1	1	1,2,3,4,5, 6,9,10,11
parameters (see 4.4)			
Group D end-point electrical	1	1	1
parameters (see 4.4)			
Group E end-point electrical			
parameters (see 4.4)			

TABLE II. Electrical test requirements.

1/ PDA applies to subgroup 1.

4.4.3 <u>Group D inspection</u>. The group D inspection end-point electrical parameters shall be as specified in table II herein.

4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table II herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table II herein.

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

DEFENSE SUPPLY CENTER COLUMBUS REVISION LEVEL SHEET	STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-94743
A 12	DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990		REVISION LEVEL A	SHEET 12

6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus (DSCC) when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.

6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA , Columbus, Ohio 43218-3990, or telephone (614) 692-0547.

6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-94743
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990		REVISION LEVEL A	SHEET 13
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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 04-06-15

Approved sources of supply for SMD 5962-94743 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard	Vendor	Vendor
microcircuit drawing	CAGE	similar
PIN <u>1</u> /	number	PIN <u>2</u> /
5962-9474301MXA	24355	AD676TD/883B

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- <u>2</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number

24355

Vendor name and address

Analog Devices Rt 1 Industrial Park PO Box 9106 Norwood, MA 02062 Point of contact: 804 Woburn Street Wilmington, MA 01887-3462

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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